

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
1	BRS	L1	628447	DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:54			0
2	BRS	L2	12833	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50			0
3	BRS	L3	3878	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:55			0
4	BRS	L4	34706	(bury or buried) near3 (layer\$1 or film\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:56			0
5	BRS	L5	753	3 and 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:40			0
6	BRS	L6	0	20040014329.URPN.	USPAT	2004/03/15 12:00			0

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	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
7	BRS	L7	268974	source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:40			0
8	BRS	L8	16200	(remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groove\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:42			0
9	BRS	L9	756023	(top or upper or second) near\$4 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:43			0
10	BRS	L10	121	5 and 7 and 8 and 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:44			0
11	BRS	L11	47376	storage\$4 near\$4 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:45			0
12	BRS	L12	53	3 and 7 and 8 and 9 and 10 and 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:49			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L13	758663	(lower or bottom or first) near\$4 (electrode\$1 or plate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:42			0
14	IS&R	L14	968	((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or (438/248) or (438/249)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:45			0
15	IS&R	L15	741	((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:46			0
16	BRS	L16	1293	14 or 15	USPAT; US-PGPUB	2004/03/15 15:47			0
17	IS&R	L17	1892	((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or (438/242) or (438/268) or (438/270) or (438/271)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:50			0
18	BRS	L18	46651	vertical\$4 near\$3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
19	BRS	L19	124	18 and 1 and 4 and 7 and 8 and 9 and (11 or 13)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:08			0
20	BRS	L20	131	17 and 1 and 18 and 9 and (11 or 13)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:09			0
21	BRS	L21	129	16 and 1 and 18 and 9 and (11 or 13)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:09			0